

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,821,829 B1  
APPLICATION NO. : 09/592349  
DATED : November 23, 2004  
INVENTOR(S) : William C. Peatman

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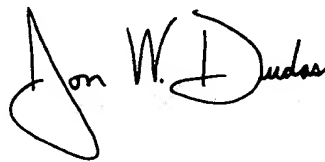
It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 8, After Line 36, Claim No. 11:

Insert --forming a dielectric layer over the gate contact, the remaining first portion of the undoped gallium arsenide capping layer and the exposed portion of the surface of the delta-doped heteroepitoxial semiconductor substrate;--

Signed and Sealed this

Twenty-sixth Day of December, 2006

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D".

JON W. DUDAS  
*Director of the United States Patent and Trademark Office*